

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ✓ Advanced trench Technology
- ✓ Low F_{OM} $R_{DS(ON)} \times Q_{gd}$

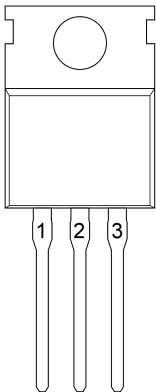
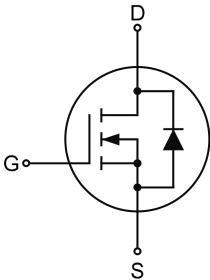
1.2 Applications

- ✓ PWM Application
- ✓ Power Management
- ✓ Load Switch

1.3 Quick reference

- ✓ $BV \geq 65\text{ V}$
- ✓ $P_D \leq 83\text{ W}$
- ✓ $I_D \leq 113\text{ A}$
- ✓ $R_{DS(ON)} \leq 3.5\text{ m}\Omega @V_{GS} = 10\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate (G)	 Top View TO-220	
2	Drain (D)		
3	Source (S)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	Drain-Source Voltage	T _C =25°C	65	-	V
V _{GS}	Gate-Source Voltage	T _C =25°C	-	±20	V
I _D	Drain Current (DC)	T _C =25°C, V _{GS} =10 V	-	113	A
		T _C =100°C, V _{GS} =10 V	-	72	A
I _{DM} *	Pulsed Source Current	T _C =25°C, V _{GS} =10 V	-	339	A
P _D	Total Power Dissipation	T _C =25°C	-	83	W
E _{AS}	Single Pulsed Avalanche Energy	V _{DD} =30 V, L=0.5 mH	-	441	mJ
T _J , T _{stg}	Operating Junction and Storage Temperature Range		-55	150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient		-	60	°C/W
R _{θJC}	Thermal Resistance-Junction to Case		-	1.5	

Notes:

- * Pulse width ≤ 300 μs, duty cycle ≤ 2%.
- ** Surface Mounted on 1 in² pad area, t ≤ 10 sec.
- *** Limited by maximum junction temperature.

4. Marking Information

Product Name	Marking
KJ0306CH	KJ0306CH XXXXXX

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ0306CH	TO-220	NA	NA	1000

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	65	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	2	-	4	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)}	On-State Resistance	V _{GS} =10 V, I _{DS} =20 A	-	3.0	3.5	mΩ
R _g	Gate Resistance	Frequency=1.0 MHz	-	2.2	-	Ω
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _{SD} =20 A, V _{GS} =0 V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _{DS} =20 A, V _{GS} =0V, dI _{SD} /dt=100 A/μs	-	46	-	ns
Q _{rr}	Reverse Recovery Charge		-	33	-	nC
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =30 V, Frequency=1.0 MHz	-	1500	-	pF
C _{oss}	Output Capacitance		-	950	-	
C _{rss}	Reverse Transfer Capacitance		-	105	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =30 V, V _{GEN} =10 V, R _G =6 Ω, I _{DS} =20 A	-	13	-	ns
t _r	Turn-on Rise Time		-	26	-	
t _{d(off)}	Turn-off Delay Time		-	30	-	
t _f	Turn-off Fall Time		-	10	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =30 V, V _{GS} =0 to 10 V, I _{DS} =20 A	-	23	-	nC
Q _{gs}	Gate-Source Charge		-	12	-	
Q _{gd}	Gate-Drain Charge		-	6	-	

7. Typical Characteristics

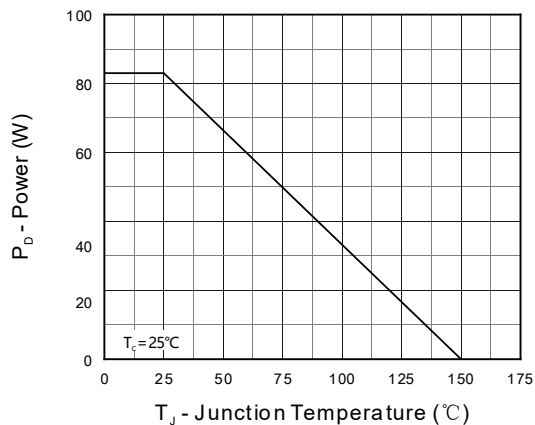


Figure 1. Power Capability

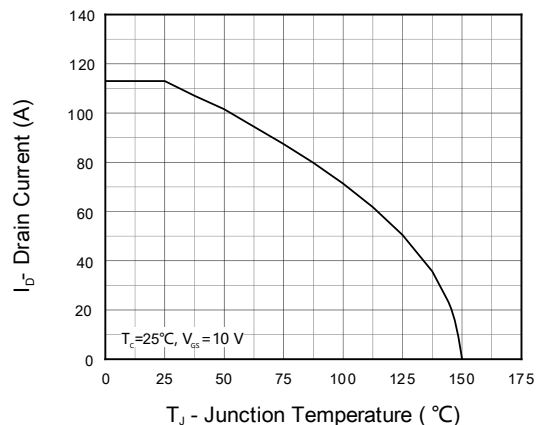


Figure 2. Current Capability

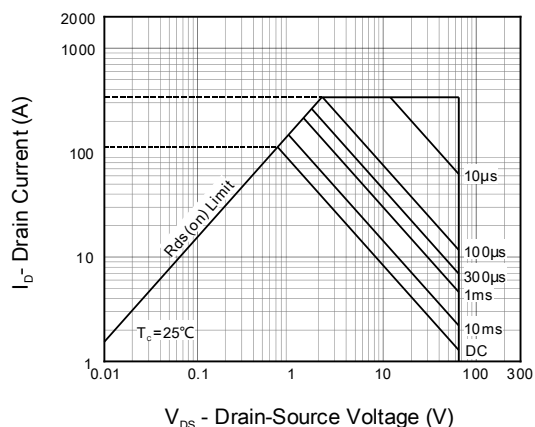


Figure 3. Safe Operation Area

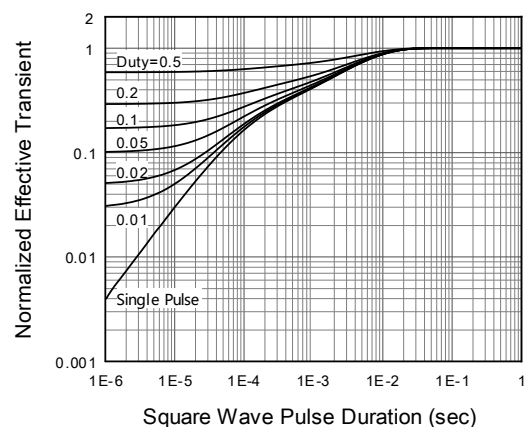


Figure 4. Transient Thermal Impedance

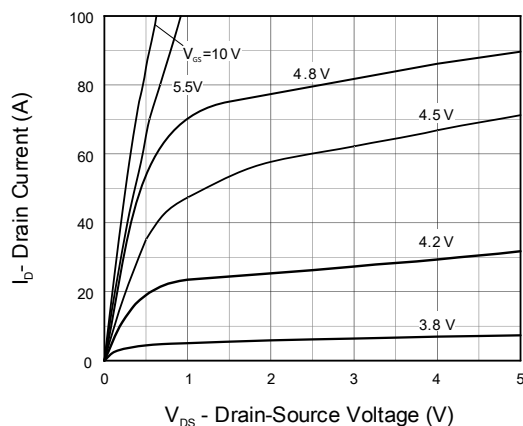


Figure 5. Output Characteristics

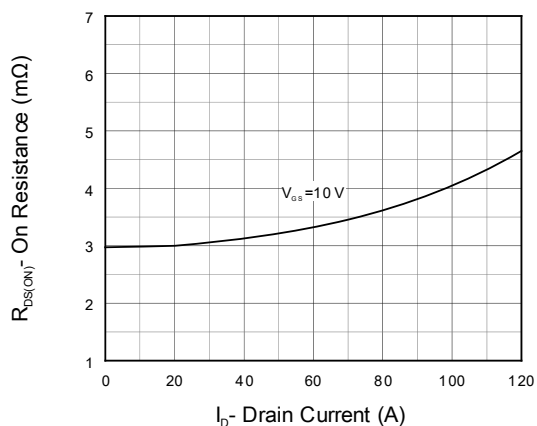


Figure 6. On Resistance

7. Typical Characteristics (cont.)

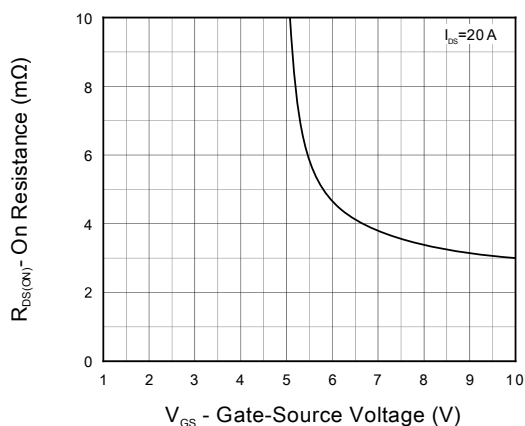


Figure 7. Transfer Characteristics

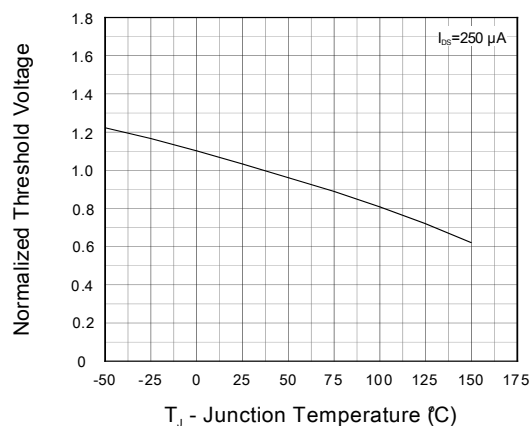


Figure 8. Normalized Threshold Voltage

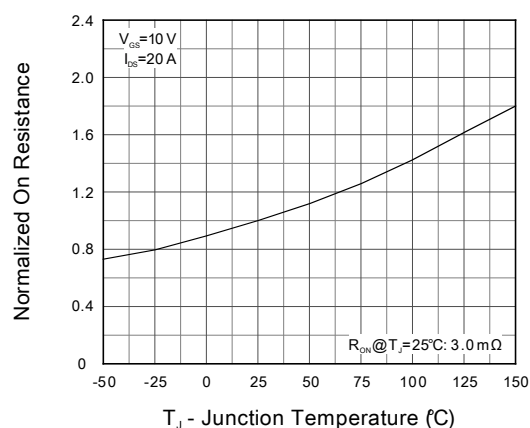


Figure 9. Normalized On Resistance

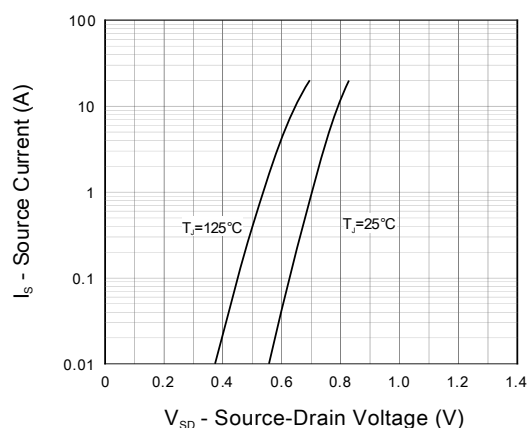


Figure 10. Diode Forward Current

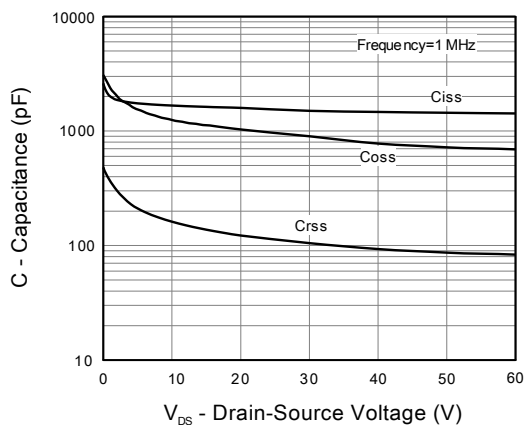


Figure 11. Capacitance

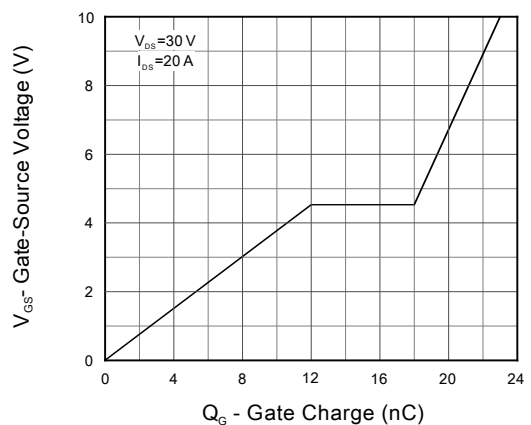
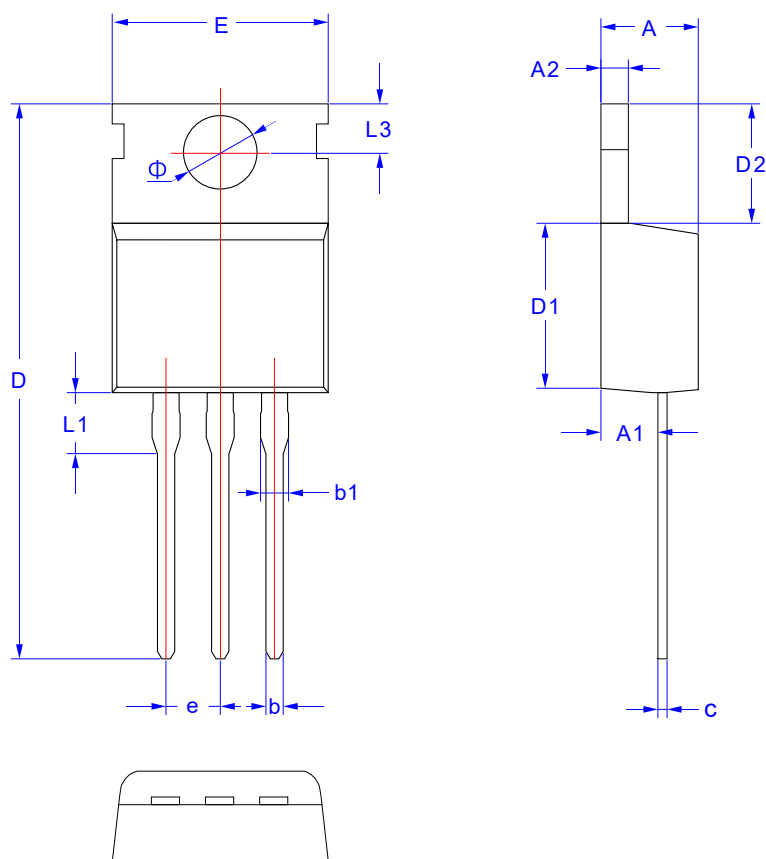


Figure 12. Gate Charge

8. Package Dimensions

TO-220 Package



Symbol	Dimensions in Millimeters	
	MIN	MAX
A	4.24	4.70
A1	2.20	3.00
b	0.70	0.95
b1	1.14	1.70
c	0.40	0.60
c1	1.15	1.40
D	28.0	29.8
D1	8.80	9.90
E	9.70	10.50
L1	3.80	
L2	6.25	6.90
L3	2.40	3.00
e	2.54 BSC	